

BAW56TT1G, SBAW56TT1G

Dual Switching Diode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Reverse Voltage	V _R	70	Vdc
Forward Current	I _F	200	mAdc
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1), T _A = 25°C Derated above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	R _{θJA}	555	°C/W
Total Device Dissipation, FR-4 Board (Note 2), T _A = 25°C Derated above 25°C	P _D	360 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	345	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 × 1.0 Inch Pad

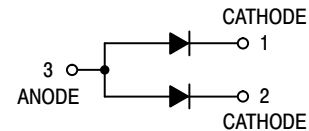


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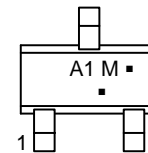
www.onsemi.com



CASE 463
SC-75/SOT-416
STYLE 4



MARKING DIAGRAM



- A1 = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAW56TT1G	SC-75/SOT-416 (Pb-Free)	3,000 / Tape & Reel
SBAW56TT1G	SC-75/SOT-416 (Pb-Free)	3,000 / Tape & Reel

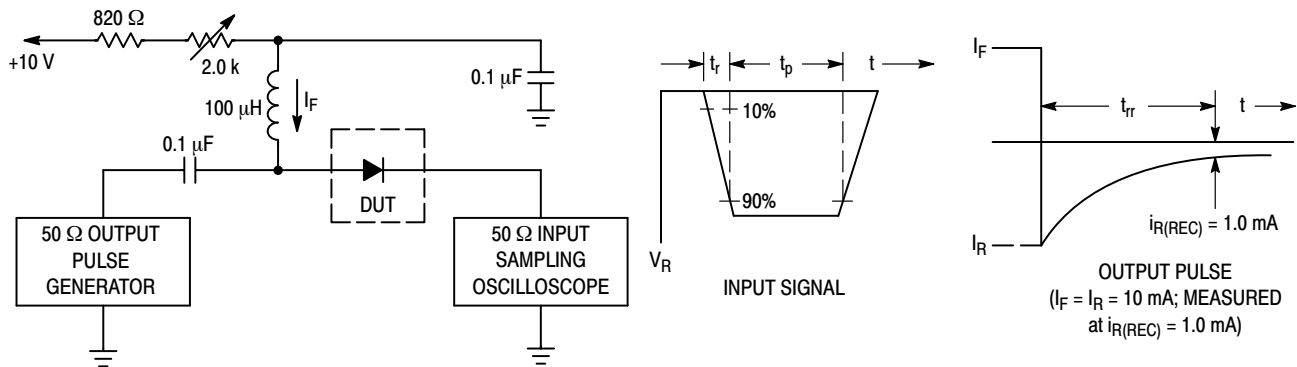
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A dc}$)	$V_{(BR)}$	70	–	Vdc
Reverse Voltage Leakage Current ($V_R = 25 \text{ Vdc}$, $T_J = 150^\circ\text{C}$) ($V_R = 70 \text{ Vdc}$) ($V_R = 70 \text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_R	– – –	30 2.5 50	$\mu\text{A dc}$
Diode Capacitance ($V_R = 0$, $f = 1.0 \text{ MHz}$)	C_D	–	2.0	pF
Forward Voltage ($I_F = 1.0 \text{ mA dc}$) ($I_F = 10 \text{ mA dc}$) ($I_F = 50 \text{ mA dc}$) ($I_F = 150 \text{ mA dc}$)	V_F	– – – –	715 855 1000 1250	mVdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA dc}$, $R_L = 100 \Omega$, $I_{R(REC)} = 1.0 \text{ mA dc}$) (Figure 1)	t_{rr}	–	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



- Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAW56TT1G, SBAW56TT1G

TYPICAL CHARACTERISTICS

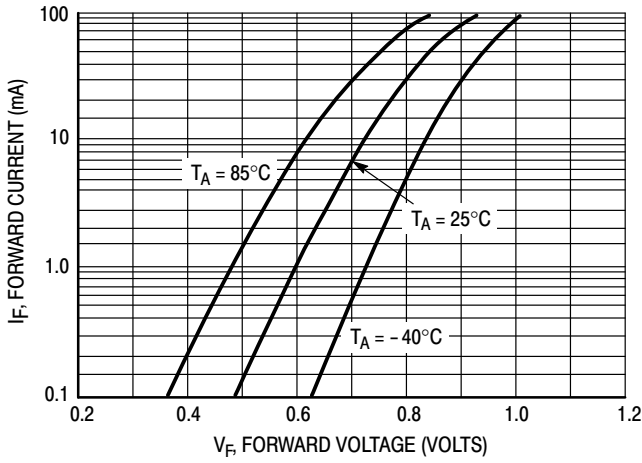


Figure 2. Forward Voltage

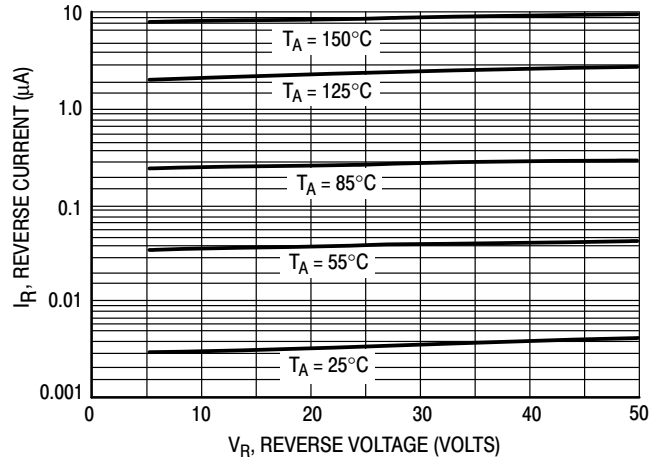


Figure 3. Leakage Current

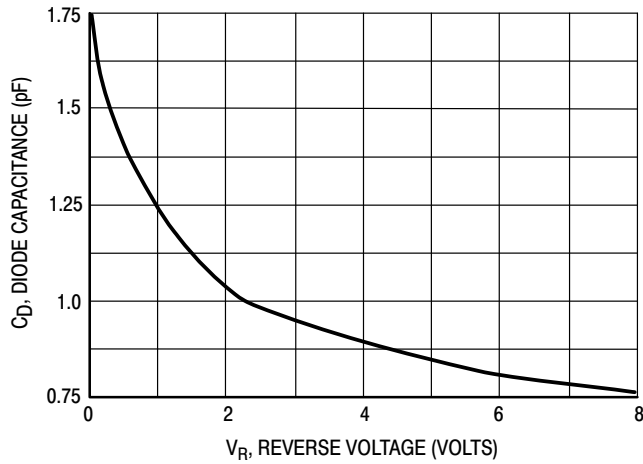


Figure 4. Capacitance

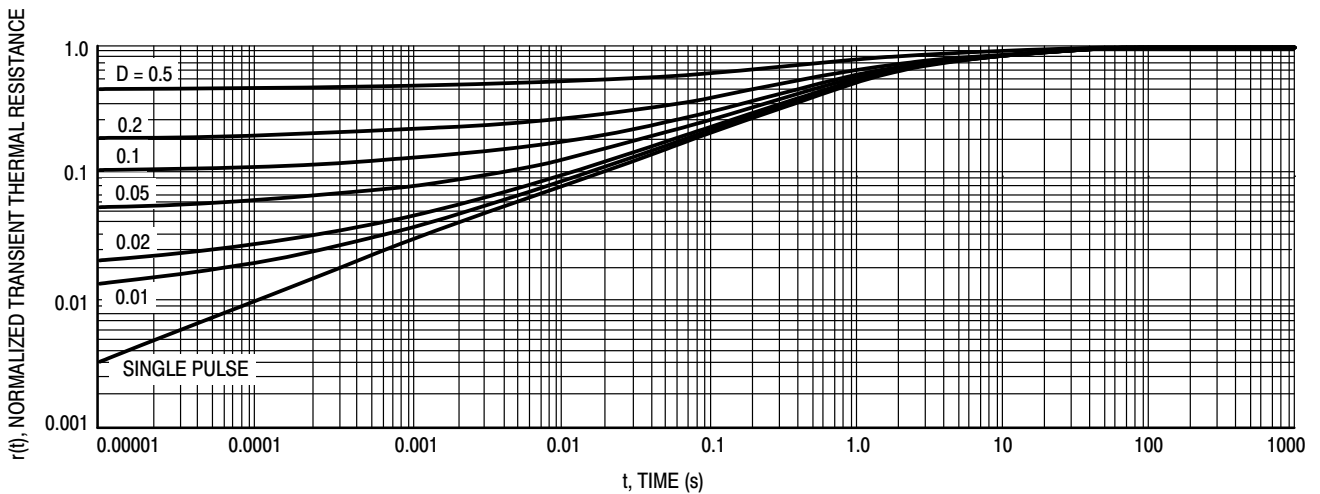
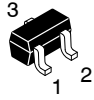


Figure 5. Normalized Thermal Response

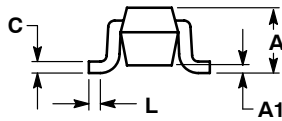
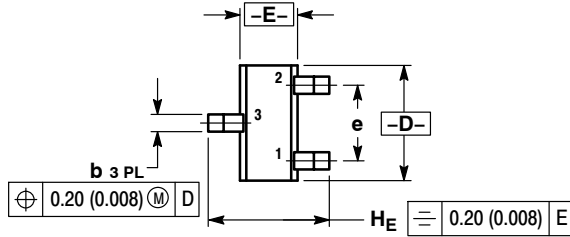
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SC-75/SOT-416
CASE 463
ISSUE G

DATE 07 AUG 2015



STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

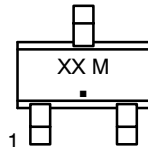
STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

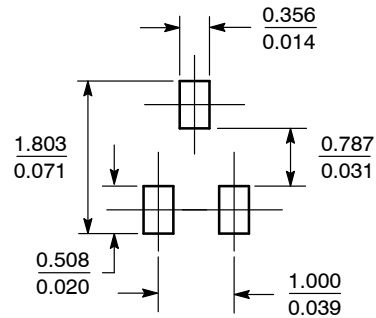
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H _E	1.50	1.60	1.70	0.060	0.063	0.067

RECOMMENDED SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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